

## SANYO Semiconductors DATA SHEET

N-Channel Silicon MOSFET

# **CPH3442** — General-Purpose Switching Device Applications

#### **Features**

- · Low ON-resistance.
- · Ultrahigh-speed switching.
- · 2.5V drive.

### **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		30	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	ID		6.5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	26	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm <sup>2</sup> X0.8mm)	1.2	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	30			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μΑ
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	0.4		1.4	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =3A	6	10		S
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =3A, V <sub>GS</sub> =4V		17	24	mΩ
	RDS(on)2	ID=1.5A, VGS=2.5V		22	31	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =10V, f=1MHz		1295		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		239		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =10V, f=1MHz		183		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit.		21		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit.		85		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		156		ns
Fall Time	tf	See specified Test Circuit.		125		ns

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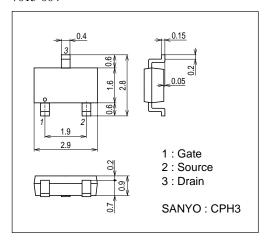
#### **CPH3442**

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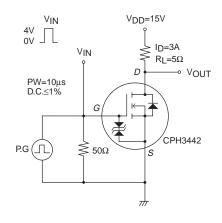
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Onn
Total Gate Charge	Qg	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =6.5A		16.1		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =6.5A		2.8		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =6.5A		5.7		nC
Diode Forward Voltage	VsD	IS=6.5A, VGS=0V		0.82	1.2	V

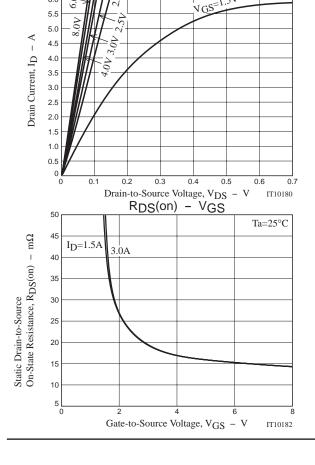
#### **Package Dimensions**

unit : mm 7015-004

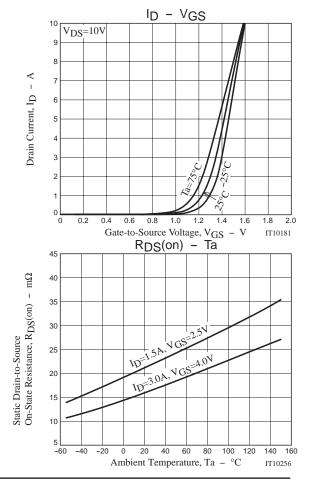


#### **Switching Time Test Circuit**

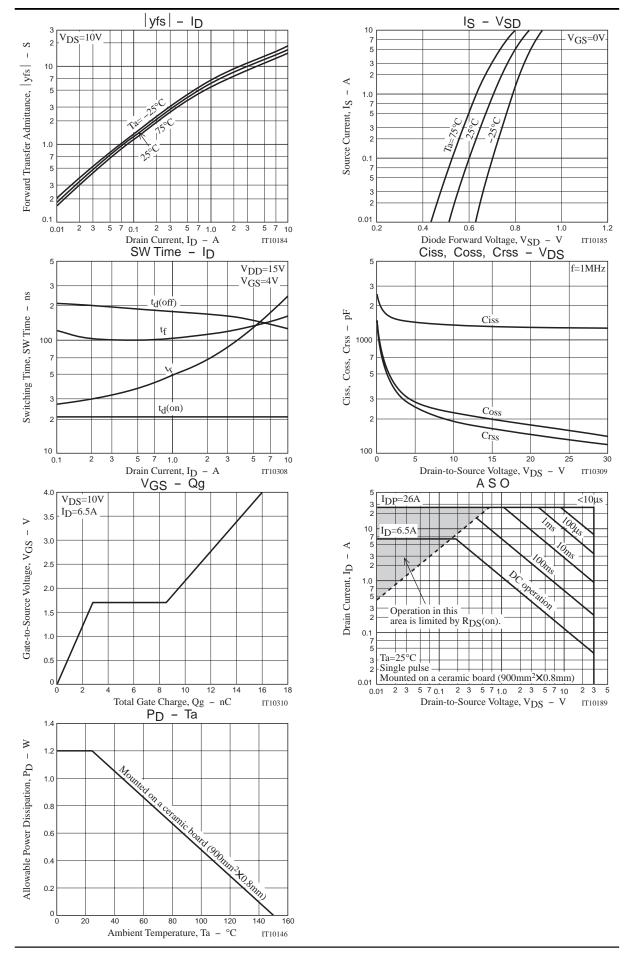




ID - VDS



No. A0094-2/4



Note on usage: Since the CPH3442 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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